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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

XE

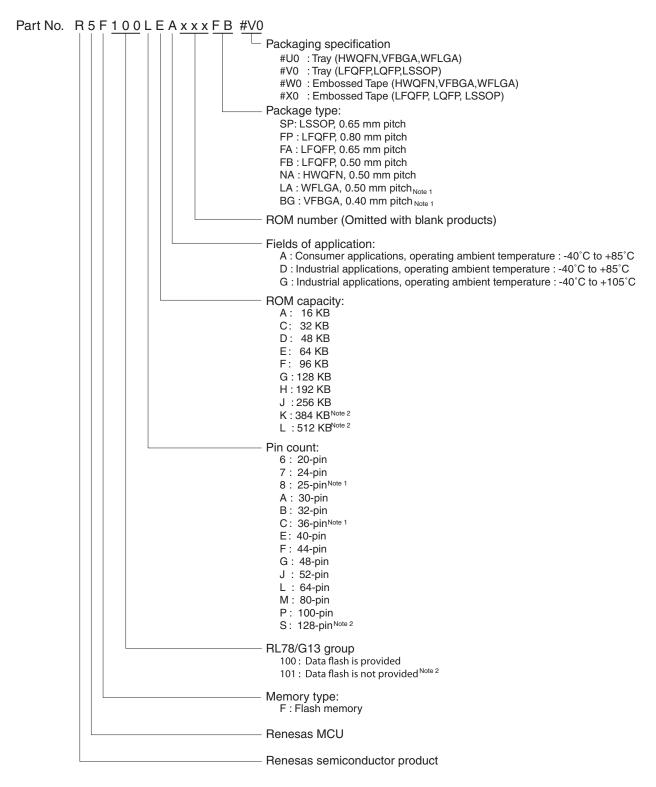
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	26
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	36-WFLGA
Supplier Device Package	36-WFLGA (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100cgala-w0

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.2 List of Part Numbers





- **Notes** 1. Products only for "A: Consumer applications ($T_A = -40$ to $+85^{\circ}C$)", and "G: Industrial applications ($T_A = -40$ to $+105^{\circ}C$)"
 - **2.** Products only for "A: Consumer applications ($T_A = -40$ to $+85^{\circ}C$)", and "D: Industrial applications ($T_A = -40$ to $+85^{\circ}C$)"



Table 1-1. List of Ordering Part Numbers

				(1/12)
Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application Note	
20 pins	20-pin plastic LSSOP	Mounted	А	R5F1006AASP#V0, R5F1006CASP#V0, R5F1006DASP#V0,
	(7.62 mm (300), 0.65			R5F1006EASP#V0
	mm pitch)			R5F1006AASP#X0, R5F1006CASP#X0, R5F1006DASP#X0,
				R5F1006EASP#X0
			D	R5F1006ADSP#V0, R5F1006CDSP#V0, R5F1006DDSP#V0,
				R5F1006EDSP#V0
				R5F1006ADSP#X0, R5F1006CDSP#X0, R5F1006DDSP#X0,
				R5F1006EDSP#X0
			G	R5F1006AGSP#V0, R5F1006CGSP#V0, R5F1006DGSP#V0,
				R5F1006EGSP#V0
				R5F1006AGSP#X0, R5F1006CGSP#X0, R5F1006DGSP#X0,
				R5F1006EGSP#X0
		Not	А	R5F1016AASP#V0, R5F1016CASP#V0, R5F1016DASP#V0,
		mounted		R5F1016EASP#V0
				R5F1016AASP#X0, R5F1016CASP#X0, R5F1016DASP#X0,
				R5F1016EASP#X0
			D	R5F1016ADSP#V0, R5F1016CDSP#V0, R5F1016DDSP#V0,
				R5F1016EDSP#V0
				R5F1016ADSP#X0, R5F1016CDSP#X0, R5F1016DDSP#X0,
				R5F1016EDSP#X0
24 pins	24-pin plastic	Mounted	А	R5F1007AANA#U0, R5F1007CANA#U0, R5F1007DANA#U0,
	HWQFN (4 $ imes$ 4mm,			R5F1007EANA#U0
	0.5 mm pitch)			R5F1007AANA#W0, R5F1007CANA#W0, R5F1007DANA#W0,
				R5F1007EANA#W0
			D	R5F1007ADNA#U0, R5F1007CDNA#U0, R5F1007DDNA#U0,
				R5F1007EDNA#U0
				R5F1007ADNA#W0, R5F1007CDNA#W0, R5F1007DDNA#W0,
				R5F1007EDNA#W0
			G	R5F1007AGNA#U0, R5F1007CGNA#U0, R5F1007DGNA#U0,
				R5F1007EGNA#U0
				R5F1007AGNA#W0, R5F1007CGNA#W0, R5F1007DGNA#W0,
				R5F1007EGNA#W0
		Not	А	R5F1017AANA#U0, R5F1017CANA#U0, R5F1017DANA#U0,
		mounted		R5F1017EANA#U0
				R5F1017AANA#W0, R5F1017CANA#W0, R5F1017DANA#W0,
				R5F1017EANA#W0
			D	R5F1017ADNA#U0, R5F1017CDNA#U0, R5F1017DDNA#U0,
				R5F1017EDNA#U0
				R5F1017ADNA#W0, R5F1017CDNA#W0, R5F1017DDNA#W0,
				R5F1017EDNA#W0

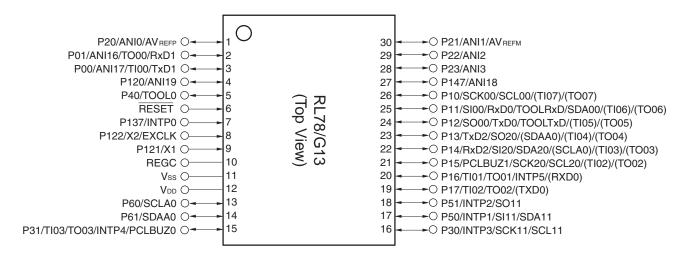
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3.4 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



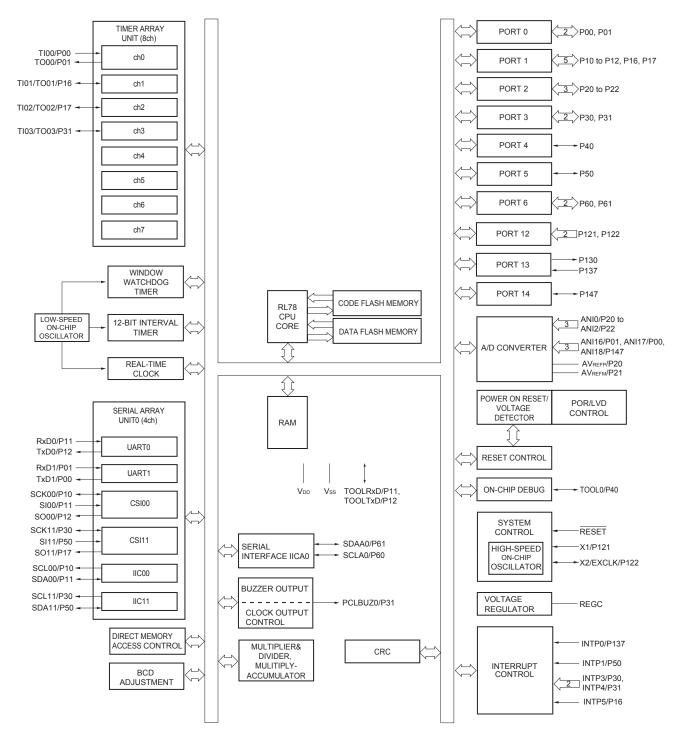
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



1.5.3 25-pin products





(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

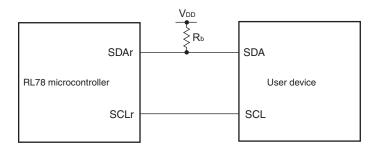
(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD2	HALT	HS (high-	$f_{IH} = 32 \text{ MHz}^{Note 4}$	$V_{DD} = 5.0 V$		0.54	1.63	mA
Current	Note 2	mode	speed main) mode ^{Note 7}		$V_{DD} = 3.0 V$		0.54	1.63	mA
				fiH = 24 MHz ^{Note 4}	$V_{DD} = 5.0 V$		0.44	1.28	mA
					V _{DD} = 3.0 V		0.44	1.28	mA
				fin = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.40	1.00	mA
					V _{DD} = 3.0 V		0.40	1.00	mA
			LS (low-	fin = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA
			speed main) mode ^{Note 7}		V _{DD} = 2.0 V		260	530	μA
			LV (low-	fiH = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		420	640	μA
			voltage main) mode		V _{DD} = 2.0 V		420	640	μA
			HS (high- speed main) mode ^{Note 7}	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.00	mA
				$V_{DD} = 5.0 V$	Resonator connection		0.45	1.17	mA
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.00	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.45	1.17	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.19	0.60	mA
				$V_{DD} = 5.0 V$	Resonator connection		0.26	0.67	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3}$,	Square wave input		0.19	0.60	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.26	0.67	mA
			LS (low- speed main) mode ^{Note 7}	$f_{MX} = 8 MHz^{Note 3}$,	Square wave input		95	330	μA
				$V_{DD} = 3.0 V$	Resonator connection		145	380	μA
				$f_{MX} = 8 MHz^{Note 3}$,	Square wave input		95	330	μA
				$V_{DD} = 2.0 V$	Resonator connection		145	380	μA
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μA
			clock	$T_A = -40^{\circ}C$	Resonator connection		0.44	0.76	μA
			operation	$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		0.30	0.57	μA
				$T_A = +25^{\circ}C$	Resonator connection		0.49	0.76	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.37	1.17	μA
				$T_A = +50^{\circ}C$	Resonator connection		0.56	1.36	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.53	1.97	μA
				$T_A = +70^{\circ}C$	Resonator connection		0.72	2.16	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.82	3.37	μA
				T _A = +85°C	Resonator connection		1.01	3.56	μA
	DD3 ^{Note 6}	STOP	$T_A = -40^{\circ}C$				0.18	0.50	μA
		mode ^{Note 8}	$T_{A} = +25^{\circ}C$				0.23	0.50	μA
			$T_A = +50^{\circ}C$				0.30	1.10	μA
			$T_A = +70^{\circ}C$				0.46	1.90	μA
			T _A = +85°C				0.75	3.30	μA

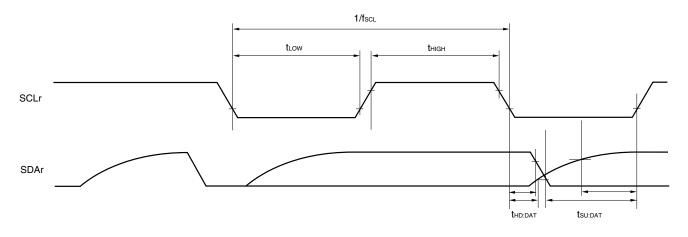
(Notes and Remarks are listed on the next page.)



Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remarks 1.** R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance
 - r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14),
 h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)



			$\sqrt{DD0} = EVDD1 \le VDD \le$						1.177	1	Lint
Parameter	Symbol		Conditions			high-		low-		low-	Unit
						main) ode	speed	main) ode		age Mode	
								1			
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$			Note		Note		Note	bps
			$2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$			1		1		1	
				Theoretical		2.8		2.8		2.8	Mbps
				value of the		Note 2		Note 2		Note 2	
				maximum							
				transfer rate							
				C _b = 50 pF, R _b =							
				$1.4 \text{ k}\Omega, V_{\text{b}} = 2.7$							
				V							
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$			Note		Note		Note	bps
			$2.3~V \leq V_b \leq 2.7~V$			3		3		3	
				Theoretical		1.2		1.2		1.2	Mbps
				value of the		Note 4		Note 4		Note 4	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$2.7 \text{ k}\Omega$, V _b = 2.3							
				V							
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$			Notes		Notes		Notes	bps
			$1.6~V \leq V_b \leq 2.0~V$			5, 6		5, 6		5, 6	
				Theoretical		0.43		0.43		0.43	Mbps
				value of the		Note 7		Note 7		Note 7	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$5.5 \text{ k}\Omega, \text{V}_{\text{b}} = 1.6$							
				V							

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2) (TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Notes 1. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV $_{DD0} \leq$ 5.5 V and 2.7 V \leq V $_{b} \leq$ 4.0 V

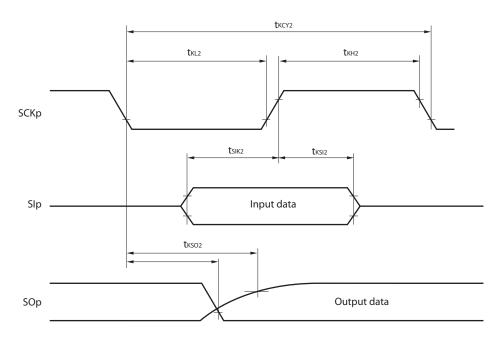
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

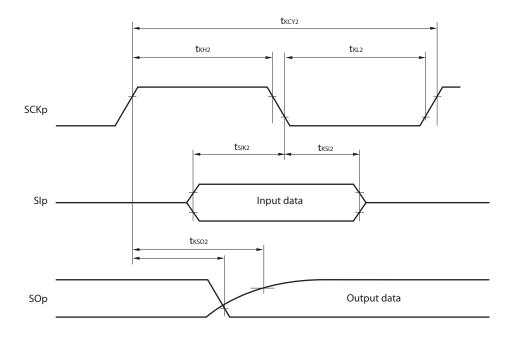
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,

n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



(2) I²C fast mode

 $(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Cor	Conditions H		h-speed Mode	``	v-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Fast mode:	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	400	0	400	0	400	kHz
		fc∟κ≥ 3.5 MHz	$1.8~V \le EV_{\text{DD0}} \le 5.5~V$	0	400	0	400	0	400	kHz
Setup time of restart	tsu:sta	$2.7 V \le EV_{DD0} \le 5.3$	5 V	0.6		0.6		0.6		μs
condition		$1.8 V \le EV_{DD0} \le 5.8$	5 V	0.6		0.6		0.6		μs
Hold time ^{Note 1}	thd:sta	$2.7 V \le EV_{DD0} \le 5.3$	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$			0.6		0.6		μs
		$1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V$		0.6		0.6		0.6		μs
Hold time when SCLA0 =	t∟ow	$2.7 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs
"L"		$1.8~V \leq EV_{\text{DD0}} \leq 5.5~V$		1.3		1.3		1.3		μs
Hold time when SCLA0 =	tніgн	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$		0.6		0.6		0.6		μs
"H"		$1.8~V \leq EV_{\text{DD0}} \leq 5.5~V$		0.6		0.6		0.6		μs
Data setup time	tsu:dat	$2.7 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$		100		100		100		μs
(reception)		$1.8~V \le EV_{\text{DD0}} \le 5.3$	5 V	100		100		100		μs
Data hold time	thd:dat	$2.7 V \le EV_{DD0} \le 5.3$	5 V	0	0.9	0	0.9	0	0.9	μs
(transmission) ^{Note 2}		$1.8 V \le EV_{DD0} \le 5.8$	5 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop	tsu:sto	$2.7 V \le EV_{DD0} \le 5.8$	5 V	0.6		0.6		0.6		μs
condition		$1.8 V \le EV_{DD0} \le 5.8$	5 V	0.6		0.6		0.6		μs
Bus-free time	t BUF	$2.7 V \le EV_{DD0} \le 5.8$	5 V	1.3		1.3		1.3		μs
		$1.8 V \le EV_{DD0} \le 5.8$	$1.8 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			1.3		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$



(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V},$
Reference voltage (+) = AVREFP, Reference voltage (–) = AVREFM = 0 V)

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$		1.2	±5.0	LSB
		$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$		1.2	±8.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \le V \text{DD} \le 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μS
		ANI26	$1.8~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V \text{DD} \leq 5.5~V$	57		95	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution EVDD0 = AV _{REFP} = V _{DD} ^{Notes 3, 4}	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
			$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note}}$			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution EVDD0 = AV _{REFP} = $V_{DD}^{Notes 3, 4}$	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
			$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Integral linearity error ^{Note}	ILE	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±3.5	LSB
1		$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±6.0	LSB
Differential linearity	DLE	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±2.0	LSB
error Note 1		$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3,4}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI26	·	0		AVREFP and EVDD0	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows. Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
- 4. When AV_{REFP} < EV_{DD0} ≤ V_{DD}, the MAX. values are as follows. Overall error: Add ±4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
- 5. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).



(2)	During communication at same potential (CSI mode) (master mode, SCKp internal clock output)
	$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS}} = \text{EV}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-spee	Unit	
				MIN.	MAX.	
SCKp cycle time	tkcy1 tkcy1 \geq 4/fclk $2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$ 250		250		ns	
			$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$	500		ns
SCKp high-/low-level width	tкнı,	$4.0~V \leq EV_{\text{DD}}$	$4.0~V \leq EV_{DD0} \leq 5.5~V$			ns
	tĸ∟ı	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$		tксү1/2 – 36		ns
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$		tксү1/2 – 76		ns
SIp setup time (to SCKp↑) Note 1	tsikı	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$		66		ns
		$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$		66		ns
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$		113		ns
SIp hold time (from SCKp \uparrow) Note 2	tksi1			38		ns
Delay time from SCKp↓ to SOp output ^{№te 3}	tkso1	$C = 30 \text{ pF}^{Note 4}$			50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

Parameter	Symbol		Condit	ions	HS (high-spee	ed main) Mode	Unit
					MIN.	MAX.	
Transfer rate		Transmission	$4.0~V \leq EV_{\text{DD0}} \leq 5.5$			Note 1	bps
		$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate		2.6 Note 2	Mbps	
			$\begin{array}{l} C_{b}=50 \; pF, \; R_{b}=1.4 \; k\Omega, \; V_{b}=2.7 \\ V \end{array} \label{eq:cb}$				
		$2.7 \ V \leq EV_{\text{DD0}} < 4.0$			Note 3	bps	
	V, 2.3 V \leq Vb \leq 2.7 V	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3$		1.2 Note 4	Mbps		
			2.4 V ≤ EV _{DD0} < 3.3	V		Note 5	bps
		V, 1.6 V \leq V _b \leq 2.0 V	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6$ V		0.43 Note 6	Mbps	

Notes 1. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV _DD0 \leq 5.5 V and 2.7 V \leq V _b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 4.0 V and 2.4 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



Parameter	Symbol	Conditions	HS (high-spe	Unit	
		[MIN.	MAX.	
SIp setup time	tsik1	$4.0 \ V \le EV_{\text{DD0}} \le 5.5 \ V, \ 2.7 \ V \le V_b \le 4.0 \ V,$	162		ns
(to SCKp↑) ^{Note}		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$			
		$2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	354		ns
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	958		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 5.5 \text{ k}\Omega$			
SIp hold time (from SCKp↑) ^{№te}	tksi1	$4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V,$	38		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$			
		$2.7 \ V \le EV_{\text{DD0}} < 4.0 \ V, \ 2.3 \ V \le V_{\text{b}} \le 2.7 \ V,$	38		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		$2.4 \ V \leq EV_{\text{DD0}} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	38		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
Delay time from SCKp \downarrow to	tkso1	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$		200	ns
SOp output ^{Note}		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$			
		$2.7 \ V \le EV_{\text{DD0}} < 4.0 \ V, \ 2.3 \ V \le V_{\text{b}} \le 2.7 \ V,$		390	ns
		$C_{\rm b}=30~pF,~R_{\rm b}=2.7~k\Omega$			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$		966	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$			

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)
 (T₁ = 40 to ±105°C 2.4 V ≤ EVere = EVere ≤ Vere ≤ 5.5 V, Vere = EVere = 6.V)

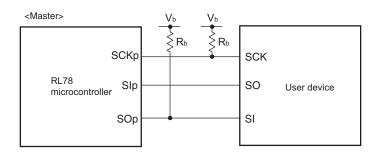
Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)



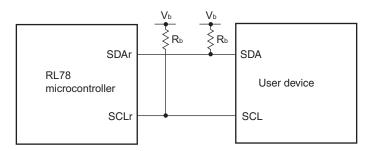
CSI mode connection diagram (during communication at different potential)



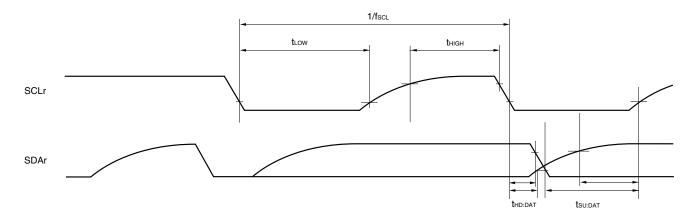
- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number , n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00, 01, 02, 10, 12, 13)



(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

 $(T_{A} = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V},$ Reference voltage (+) = AV_{\text{REFP}}, Reference voltage (-) = AV_{\text{REFM}} = 0 \text{ V})

Parameter	Symbol	Conditior	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	$\begin{array}{l} 10\text{-bit resolution} \\ EV_{DD0} \leq AV_{\text{REFP}} = V_{\text{DD}} ^{\text{Notes 3, 4}} \end{array}$	$\begin{array}{l} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$		1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.125		39	μs
		Target pin : ANI16 to ANI26	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μs
		$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs	
Zero-scale error ^{Notes 1, 2}	Ezs	$\begin{array}{l} \mbox{10-bit resolution} \\ \mbox{EVDD0} \leq AV_{\text{REFP}} = V_{\text{DD}} ^{\text{Notes 3, 4}} \end{array}$	$\begin{array}{l} 2.4 \ V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Efs	$\begin{array}{l} \text{10-bit resolution} \\ \text{EVDD0} \leq AV_{\text{REFP}} = V_{\text{DD}} \\ \end{array} \end{array}$	$\begin{array}{l} 2.4 \ V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $EV \text{DD0} \leq AV_{\text{REFP}} = V_{\text{DD}}^{\text{Notes 3, 4}}$	$\begin{array}{l} 2.4 \ V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±3.5	LSB
Differential linearity error	DLE	$\begin{array}{l} 10\text{-bit resolution} \\ EV \text{DD0} \leq AV_{\text{REFP}} = V_{\text{DD}} ^{\text{Notes 3, 4}} \end{array}$	$\begin{array}{l} 2.4 \ V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI26		0		AVREFP and EVDD0	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- When AV_{REFP} < V_{DD}, the MAX. values are as follows. Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 When AV_{REFP} < EV_{DD0} ≤ V_{DD}, the MAX. values are as follows.
- 4. When AVREFP < EVDDO S VDD, the MAX. values are as follows. Overall error: Add ±4.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.



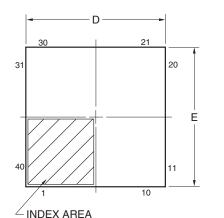
4.7 40-pin Products

R5F100EAANA, R5F100ECANA, R5F100EDANA, R5F100EEANA, R5F100EFANA, R5F100EGANA, R5F100EHANA R5F101EAANA, R5F101ECANA, R5F101EDANA, R5F101EEANA, R5F101EFANA, R5F101EGANA, R5F101EHANA R5F100EADNA, R5F100ECDNA, R5F100EDDNA, R5F100EEDNA, R5F100EFDNA, R5F100EGDNA, R5F100EHDNA

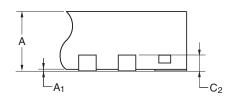
R5F101EADNA, R5F101ECDNA, R5F101EDDNA, R5F101EEDNA, R5F101EFDNA, R5F101EGDNA, R5F101EHDNA

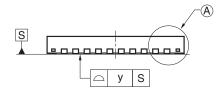
R5F100EAGNA, R5F100ECGNA, R5F100EDGNA, R5F100EEGNA, R5F100EFGNA, R5F100EGGNA, R5F100EHGNA

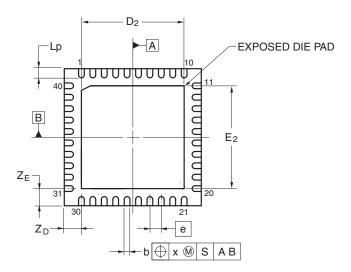
JEITA Package code	RENESAS code	Previous code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-5	0.09



Detail of (A) Part







Referance Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	5.95	6.00	6.05
E	5.95	6.00	6.05
A			0.80
A ₁	0.00		
b	0.18	0.25	0.30
е		0.50	
Lp	0.30	0.40	0.50
х			0.05
у			0.05
ZD		0.75	—
Z _E		0.75	—
C ₂	0.15	0.20	0.25
D ₂		4.50	
E ₂		4.50	

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4.10 52-pin Products

R5F100JCAFA, R5F100JDAFA, R5F100JEAFA, R5F100JFAFA, R5F100JGAFA, R5F100JHAFA, R5F100JJAFA, R5F100JLAFA

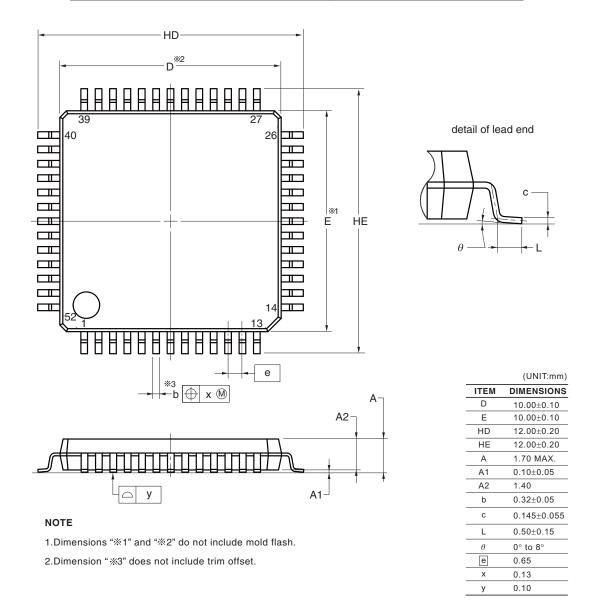
R5F101JCAFA, R5F101JDAFA, R5F101JEAFA, R5F101JFAFA, R5F101JGAFA, R5F101JHAFA, R5F101JJAFA, R5F101JLAFA

R5F100JCDFA, R5F100JDDFA, R5F100JEDFA, R5F100JFDFA, R5F100JGDFA, R5F100JHDFA, R5F100JJDFA, R5F100JLDFA

R5F101JCDFA, R5F101JDDFA, R5F101JEDFA, R5F101JFDFA, R5F101JGDFA, R5F101JHDFA, R5F101JJDFA, R5F101JLDFA

R5F100JCGFA, R5F100JDGFA, R5F100JEGFA, R5F100JFGFA, R5F100JGGFA, R5F100JHGFA, R5F100JJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



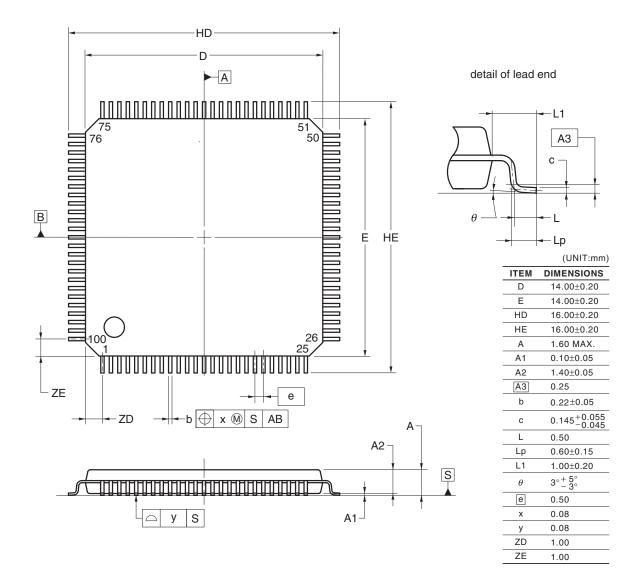
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4.13 100-pin Products

R5F100PFAFB, R5F100PGAFB, R5F100PHAFB, R5F100PJAFB, R5F100PKAFB, R5F100PLAFB R5F101PFAFB, R5F101PGAFB, R5F101PHAFB, R5F101PJAFB, R5F101PKAFB, R5F101PLAFB R5F100PFDFB, R5F100PGDFB, R5F100PHDFB, R5F100PJDFB, R5F100PKDFB, R5F100PLDFB R5F101PFDFB, R5F101PGDFB, R5F101PHDFB, R5F101PJDFB, R5F101PKDFB, R5F101PLDFB R5F100PFGFB, R5F100PGGFB, R5F100PHGFB, R5F100PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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